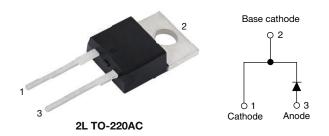
Vishay Semiconductors

www.vishay.com

Hyperfast Rectifier, 8 A FRED Pt[®] G5



LINKS TO ADDITIONAL RESOURCES



| PRIMARY CHARACTERISTICS | | | | |
|--|-------------|--|--|--|
| I _{F(AV)} | 8 A | | | |
| V _R | 1200 V | | | |
| V _F at I _F at 125 °C | 1.8 V | | | |
| t _{rr} | 33 ns | | | |
| T _J max. | 175 °C | | | |
| Package | 2L TO-220AC | | | |
| Circuit configuration | Single | | | |

FEATURES

- Hyperfast and optimized Q_{rr}
- Best in class forward voltage drop and switching RoHS
 losses trade off
 HALOGEN
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MECHANICAL DATA

Case: 2L TO-220AC

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Polarity: as per marking device details

| ABSOLUTE MAXIMUM RATINGS | | | | | |
|--|-----------------------------------|---|-------------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | |
| Repetitive peak reverse voltage | V _{RRM} | | 1200 | V | |
| Average rectified forward current | I _{F(AV)} | T _C = 122 °C, D = 0.50 | 8 | | |
| Repetitive peak forward current | I _{FRM} | T _C = 122 °C, D = 0.50, f = 20 kHz | 16 | А | |
| Non-repetitive peak surge current | I _{FSM} | T_{C} = 45 °C, t_{p} = 10 ms, sine wave | 65 | | |
| Operating junction and storage temperature | T _J , T _{Stg} | | -55 to +175 | °C | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|--|-------------------------------------|---|------|------|-------|-------|--|
| PARAMETER | SYMBOL | . TEST CONDITIONS MIN. TYP. | | MAX. | UNITS | | |
| Breakdown voltage, blocking voltage | V _{BR} , V _R | I _R = 100 μA | 1200 | - | - | | |
| Forward voltage | V _F | I _F = 8 A | - | 1.9 | 2.5 | V | |
| | | I _F = 8 A, T _J = 125 °C | - | 1.8 | - | | |
| R | I _R | $V_{R} = V_{R}$ rated | - | - | 50 | | |
| Reverse leakage current | | $T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$ | - | - | 500 | 00 μA | |
| Junction capacitance | CT | C _T V _R = 200 V - 5 - | | - | pF | | |
| Series inductance | L _S | Measured to lead 5 mm from package body | - | 8 | - | nH | |

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| DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified) | | | | | | | |
|---|------------------|---|---|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| | | $I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$ | | - | 33 | 55 | |
| Reverse recovery time | t _{rr} | T _J = 25 °C | | - | 100 | - | ns |
| | | T _J = 125 °C | | - | 165 | - | |
| Peak recovery current | I== | T _J = 25 °C | I _F = 6 A dI _F /dt = 400 A/μs V _R = 400 V | - | 8.0 | - | A |
| Peak recovery current | I _{RRM} | T _J = 125 °C | | - | 10 | - | |
| Reverse recovery charge | 0 | T _J = 25 °C | | - | 300 | - | nC |
| | Q _{rr} | T _J = 125 °C | | - | 700 | - | |
| Reverse recovery time | + | T _J = 25 °C | | - | 60 | - | ns |
| neverse recovery time | t _{rr} | T _J = 125 °C | | - | 80 | - | 115 |
| Peak recovery current | | T _J = 25 °C | I _F = 8 A dI _F /dt = 1000 A/μs V _R = 800 V | - | 16 | - | A |
| | I _{RRM} | T _J = 125 °C | | - | 26 | - | |
| Reverse recovery charge | 0 | T _J = 25 °C | | - | 570 | - | nC |
| | Q _{rr} | T _J = 125 °C | | - | 1350 | - | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|-----------------------------------|------------------------|--------------|------|------------|------------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Thermal resistance, junction-to-case | R _{thJC} | | - | - | 2.3 | °C/W |
| Weight | | | - | 2 | - | g |
| | | | - | 0.07 | - | oz. |
| Mounting torque | | | 6.0 (5.0) | - | 12 (10) | kgf · cm (lbf · in) |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -55 | - | 175 | °C |
| Marking device | | Case style 2L TO-220AC | | E5TH | 10812 | |



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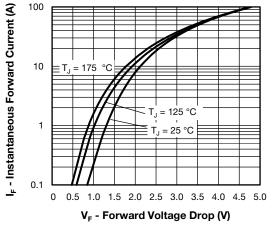


Fig. 1 - Forward Voltage Drop Characteristics

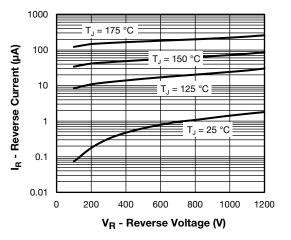


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

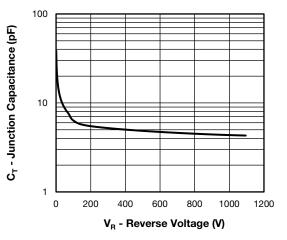


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

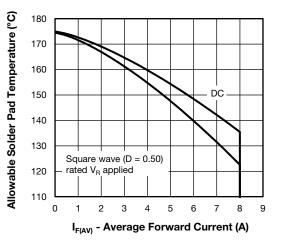


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

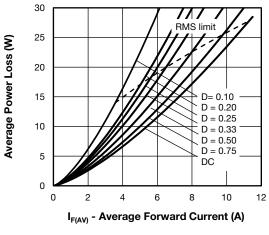


Fig. 5 - Forward Power Loss Characteristics

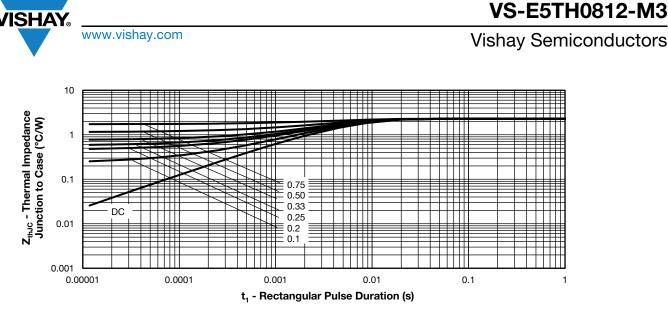


Fig. 6 - Transient Thermal Impedance, Junction to Case

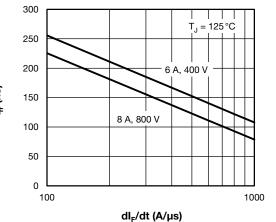


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

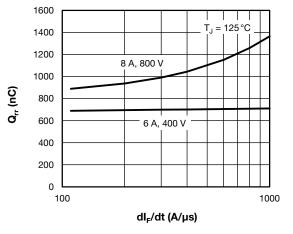


Fig. 8 - Typical Stored Charge vs. dl_F/dt

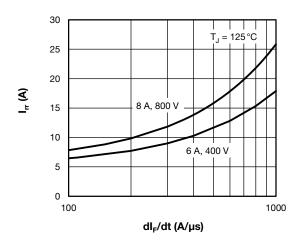


Fig. 9 - Typical Recovery Current vs. dI_F/dt

t_{rr} (ns)





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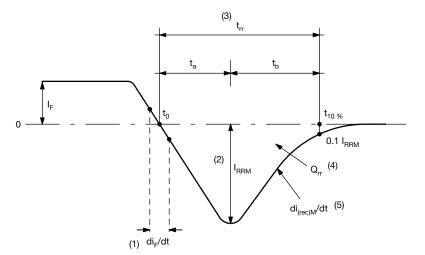


Fig. 10 - Reverse Recovery Waveform and Definitions

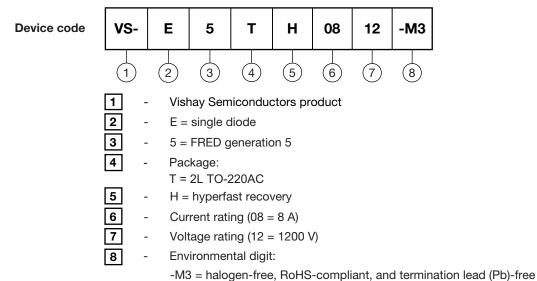
Notes

- (1) di_F/dt rate of change of current through zero crossing
- ⁽²⁾ I_{RRM} peak reverse recovery current
- $^{(3)}$ t_{rr} reverse recovery time measured from t₀, crossing point of negative going I_F, to point t_{10%}, 0.1 I_{RRM}
- $^{(4)}~~Q_{rr}$ area under curve defined by t_0 and $t_{10~\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t)dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE



| ORDERING INFORMATION (Example) | | | | | | | |
|--------------------------------|--|------|-------------------------|--|--|--|--|
| PREFERRED P/N | PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION | | | | | | |
| VS-E5TH0812-M3 | 50 | 1000 | Antistatic plastic tube | | | | |

| LINKS TO RELATED DOCUMENTS | | | |
|----------------------------|--------------------------|--|--|
| Dimensions | www.vishay.com/doc?96154 | | |
| Part marking information | www.vishay.com/doc?95391 | | |
| | | | |

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